Electrical Characteristics (T_C=25 unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	650	/	/	V	V_{GS}=0V, I_D=1mA	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.9	4.0	V	V_{DS}=V_{GS}, I_D=7.5mA	Fig. 11
		/	2.1	/		V_{DS}=V_{GS}, I_D=7.5mA, T_J=175	
I_{DSS}	Zero Gate Voltage Drain Current	/	1	100	μA	V_{DS}=650V, V_{GS}=0V	
I_{GSS+}	Gate-Source Leakage Current	/	10	100	nA	V_{DS}=0V, V_{GS}=23V	
I_{GSS-}	Gate-Source Leakage Current	/	10	100	nA	V_{DS}=0V, V_{GS}=-10V	V

Typical Performance

Figure 1. Output Characteristics T_J = -55

Figure 2. Output Characteristics T_J = 25

Figure 3. Output Characteristics T_J = 175

Figure 4. Normalized On-

Typical Performance

Figure 7. Transfer Characteristic for Various Junction Temperatures

Figure 8. Body Diode Characteristic at -55

Figure 9. Body Diode Characteristic at 25

Figure 10. Body Diode Characteristic at 175

Figure 11.

Typical Performance

Figure 13. 3rd Quadrant Characteristic at -55

Test Circuit Schematic

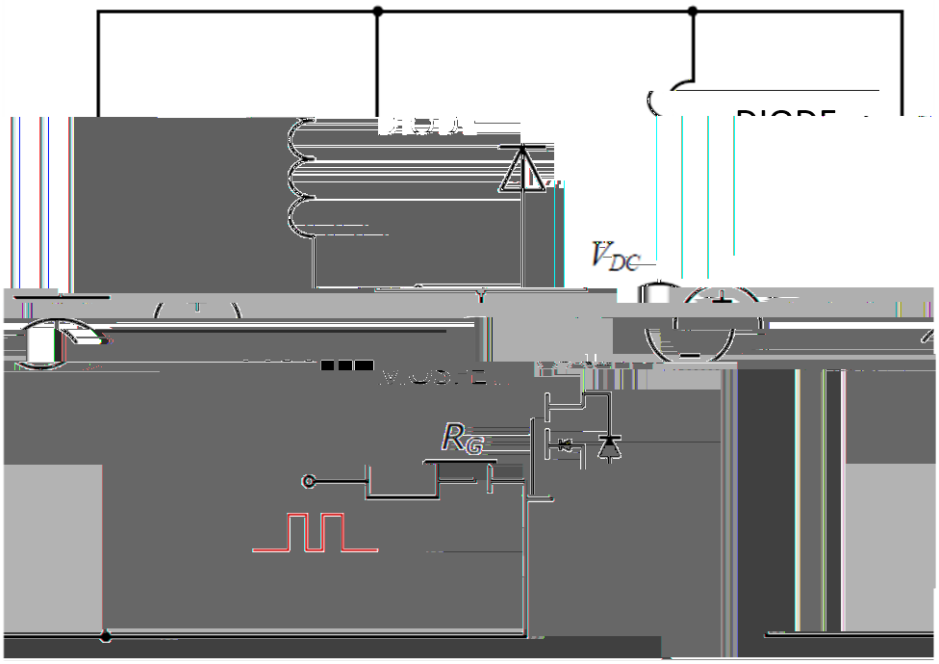
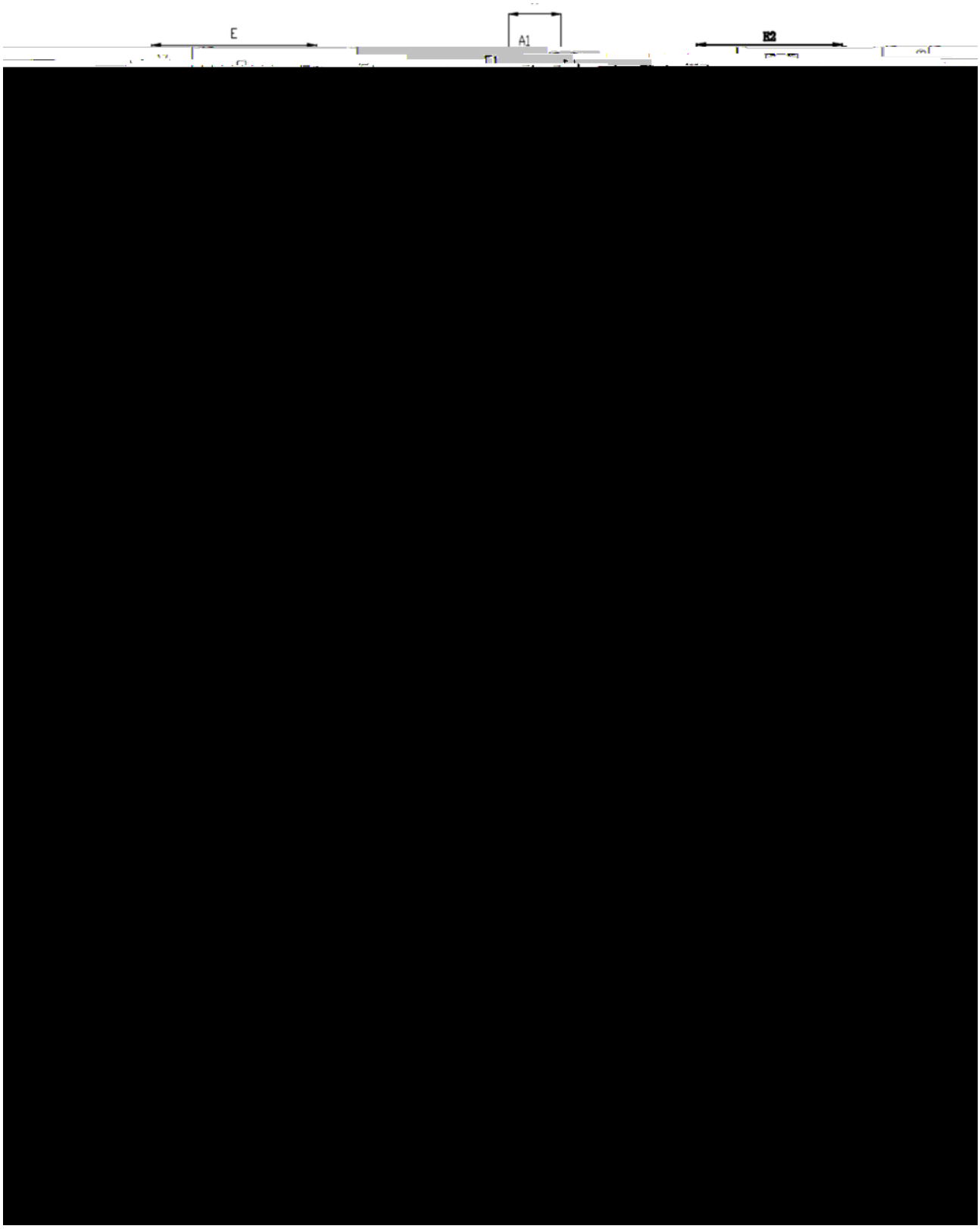


Figure 23. Clamped Inductive Switching Waveform Test Circuit

Package Dimensions



Notes

1) Before using our products, please contact our marketing managers and get the latest specifications.

2) Ongoing efforts are being made to improve the reliability and quality of the products by CETC, but the semiconductors can malfunction due to various factors. Therefore, in order to prevent artificial damage or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. CETC doesn't have responsibility for any damages arising from the use of our products bey0d0.003 Tw w1 ofe71 1 T5(i)-45(n)-27(g r)-3915 Tw 9.12 0 0 Tw 9(i)9(f)12(i)e1(an)27(dby12(s)-3(14(C)8(E

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